

Single-Phase Voltage Regulator with SVID

High Efficiency, Integrated Power MOSFETs

NCP3285F, NCP3285AF

The NCP3285F/AF, a single-phase synchronous buck regulator with SVID, integrates power MOSFETs to provide a high-efficiency and compact-footprint power management solution. The NCP3285F/AF is able to deliver up to 20 A / 35 A TDC output current on a wide output voltage range. Operating in high switching frequency up to 1 MHz allows employing small size inductors and capacitors while maintaining high efficiency due to integrated solution with high performance power MOSFETs. It provides differential voltage sense and comprehensive protections.

Features

- $V_{in} = 4.5\text{ V} \sim 18\text{ V}$
- $V_{out} = 0.5\text{ V} \sim 2.0\text{ V}$ to Support Intel VR13, VR13.HC and VR14 SVID
- Integrated Power MOSFETs
- Up to 20 A (NCP3285F)/35 A (NCP3285AF) Continuous Output Current and 35 A (NCP3285F)/45 A (NCP3285AF) Pulse Current
- Integrated 5 V LDO or External 5 V Supply
- Enable with Programmable V_{in} UVLO
- 400 k/600 k/800 k/1000 kHz Switching Frequency
- Selectable Forced CCM and Auto DCM/CCM
- 16 Selectable Boot Voltages
- 12 Selectable SVID Addresses
- Output Discharge in Shutdown
- Programmable Current Limit
- Latch-Off Over-Voltage and Under-Voltage Protection
- Recoverable Thermal Shutdown Protection
- PQFN37, 5x6 mm, 0.5 mm Pitch Package
- This is a Pb-Free Device

Typical Applications

- Point of Load
- Computing Applications
- Telecom and Networking
- Server and Storage System

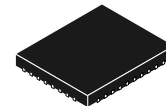
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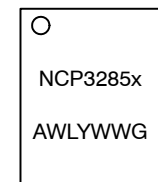
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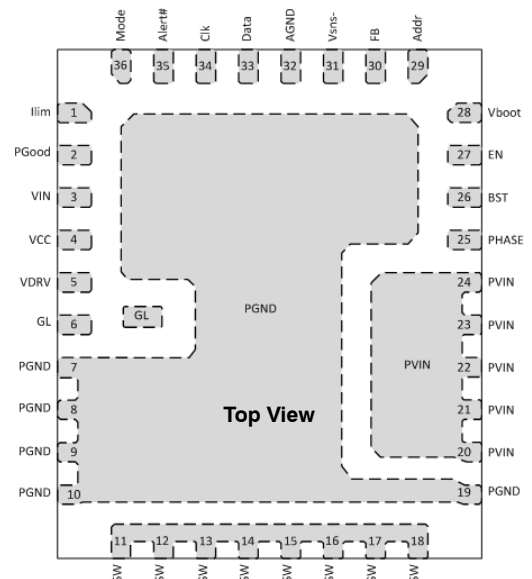
PQFN37 5x6, 0.5P
CASE 483BZ

MARKING DIAGRAM



NCP3285x = Specific Device Code
 $\Rightarrow x = F \text{ or } AF$
 A = Assembly Site
 WL = Wafer Lot Number
 Y = Year of Production
 WW = Work Week Number
 G = Pb-Free Designator

PINOUT



ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ORDERING INFORMATION

Device	Package	Shipping
NCP3285FMNTXG, NCP3285AFMNTXG	PQFN37 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

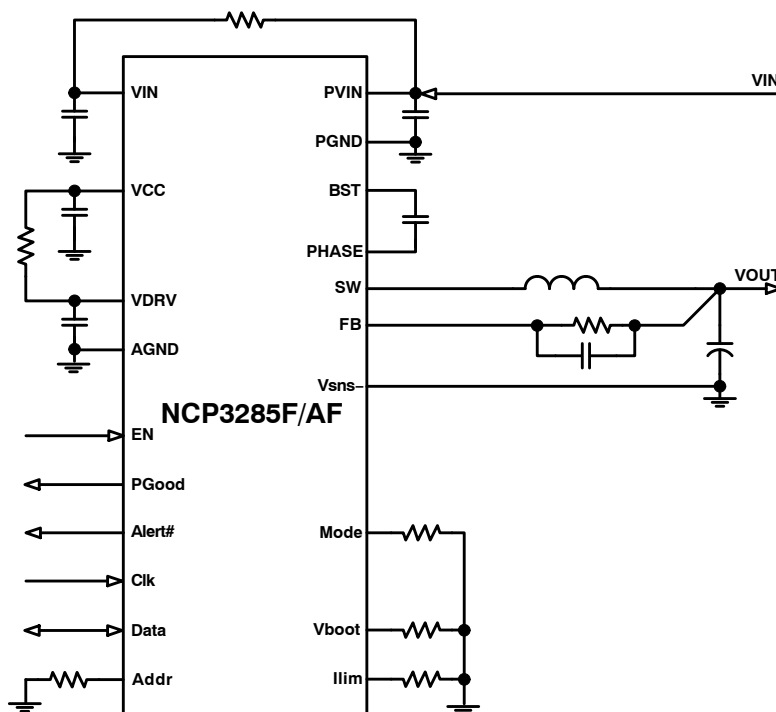


Figure 1. Typical Application Circuit with Single Input Power Supply (LDO Enabled)

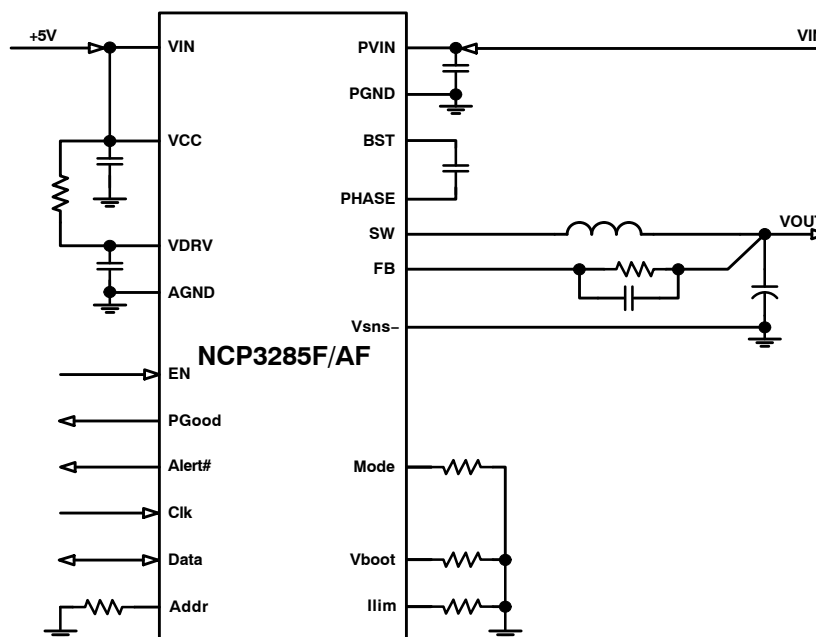


Figure 2. Typical Application Circuit with External 5V Supply for VCC (LDO Disabled)

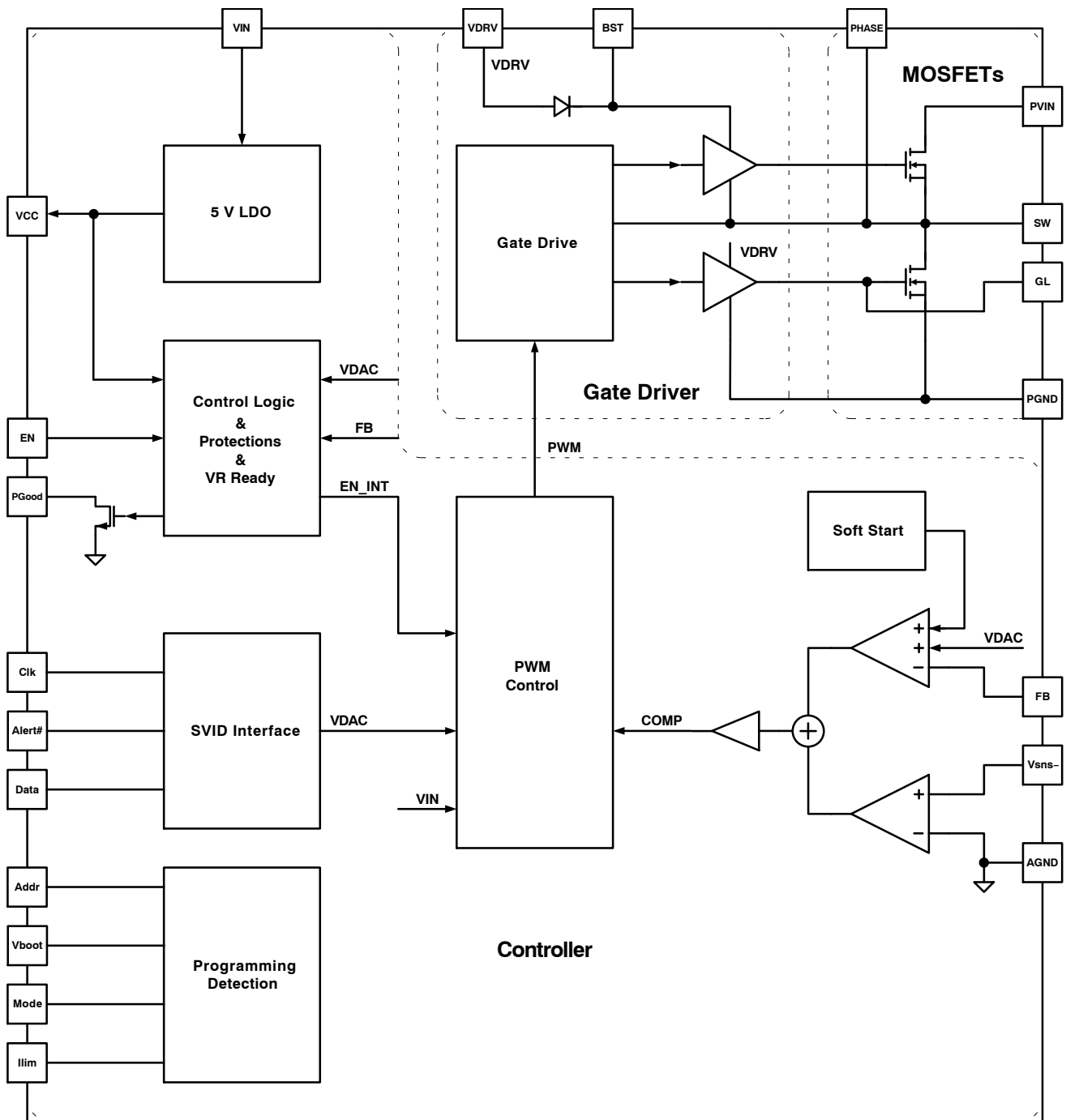


Figure 3. Functional Block Diagram

PIN DESCRIPTION

Pin	Name	Type	Description
1	Ilim	Analog Output	Current Limit. A resistor between this pin and AGND to program current limit
2	PGood	Logic Output	Power GOOD. Open-drain output. Provides a logic high valid power good output signal, indicating the regulator's output is in regulation window
3	VIN	Power Input	Power Supply Input of LDO. Power supply input pin of internal 5 V LDO. A 1.0 μ F or more ceramic capacitors must bypass this input to power ground. The capacitors should be placed as close as possible to this pin. A direct short from this pin to VCC (pin 4) disables the internal LDO for applications with an external 5 V supply as power of VCC and VDRV
4	VCC	Analog Power	Output of LDO and Supply Voltage Input of Controller. A 2.2 μ F or larger ceramic capacitor bypasses this input to GND. This capacitor should be placed as close as possible to this pin
5	VDRV	Analog Power	Supply Voltage Input of Gate Drivers. A 4.7 μ F/25 V or larger ceramic capacitor bypasses this input to PGND. This capacitor should be placed as close as possible to this pin
6	GL	Analog Output	Gate of Low-Side MOSFET. Directly connected with the gate of the low-side power MOSFET
7~10,19	PGND	Power Ground	Power Ground. These pins are the power supply ground pins of the device, which are connected to source of internal low-side power MOSFET. Must be connected to the system ground
11~18	SW	Power Bidirectional	Switch Node. Pins to be connected to an external inductor. These pins are inter-connection between internal high-side MOSFET and low-side MOSFET
20~24	PVIN	Power Input	Power Supply Input. These pins are the power supply input pins of the device, which are connected to drain of internal high-side power MOSFET. A 22 μ F or more ceramic capacitors must bypass this input to PGND. The capacitors should be placed as close as possible to these pins
25	PHASE	Power Return	Phase Node. Provides a return path for integrated high-side gate driver. It is internally connected to source of high-side MOSFET
26	BST	Power Bidirectional	Bootstrap. Provides bootstrap voltage for high-side gate driver. A 0.22 μ F/25 V ceramic capacitor is required from this pin to PHASE (pin 25)
27	EN	Logic Input	Enable. Logic high enables controller while logic low disables controller. Input supply UVLO can be programmed at this pin
28	Vboot	Analog Input	Boot-Up Voltage. A resistor from this pin to ground programs boot-up voltage
29	Addr	Analog Input	Multi-Function pin for SVID Address, Frequency, WP_Slew_TT Register(5Bh) and Protocol ID Register (05h): A resistor from this pin to ground programs SVID address, 400 kHz frequency, different default value of REG5Bh and Protocol ID REG05h
30	FB	Analog Input	Feedback. Inverting input to error amplifier
31	Vsns-	Analog Input	Voltage Sense Negative Input. Connect this pin to remote voltage negative sense point
32	AGND	Analog Ground	Analog Ground. Ground of controller. Must be connected to the system ground
33	Data	Logic Bidirectional	Serial Data IO Port. Data port of SVID interface
34	Clk	Logic Input	Serial Clock. Clock input of SVID interface
35	Alert#	Logic Output	ALERT#. Open-drain output. Provides a logic low valid alert signal of SVID interface
36	Mode	Analog Input	Mode. A resistor between this pin and AGND to program operation mode, nominal switching frequency, and options

MAXIMUM RATINGS

Rating	Symbol	Value		Unit
		MIN	MAX	
Power Supply Voltage to PGND	V_{PVIN}, V_{VIN}	-0.3	25	V
SW to PGND, PHASE to PGND	V_{SW}, V_{PHASE}	-0.6 -5 (<50 ns)	25 28 (<10 ns)	V
PVIN to SW/PHASE	$V_{PVIN-PHS}$	-0.3 -5 (<10 ns)	25 33 (<10 ns)	V
Driver Supply Voltage to PGND	VDRV	-0.3	6.5	V
Analog Supply Voltage to AGND	VCC	-0.3	6.5	V
BST to PGND	BST_PGND	-0.3	30 33 (<50 ns)	V
BST to PHASE	BST_PHASE/SW	-0.3	6.5	V
GL to PGND	GL	-0.3 -2 (<200 ns)	VDRV+0.3	V
VSNS- to AGND	VSNS-	-0.2	0.2	V
PGND to AGND	PGND	-0.3	0.3	V
Other Pins		-0.3	VCC+0.3	V
Operating Junction Temperature Range	T_J	-40	125	°C
Operating Ambient Temperature Range	T_A	-40	100	°C
Storage Temperature Range	T_{STG}	-55	150	°C
Thermal Resistance Junction to Top Case (Note 1)	$R_{\Psi JC}$	1.0 (NCP3285F) 0.8 (NCP3285AF)		°C/W
Thermal Resistance Junction to Board (Note 1)	$R_{\Psi JB}$	1.2 (NCP3285F) 0.9 (NCP3285AF)		°C/W
Thermal Resistance Junction to Ambient (Note 1)	$R_{\theta JA}$	27.0 (NCP3285F) 26.7 (NCP3285AF)		°C/W
Maximum Power Dissipation (Note 2)	P_D	3.70 (NCP3285F) 3.75 (NCP3285AF)		W
Moisture Sensitivity Level (Note 3)	MSL	1		–

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The thermal resistance values are dependent of the internal losses split between devices and the PCB heat dissipation. This data is based on a typical operation condition with a 4-layer FR-4 PCB board, which has two, 1-ounce copper internal power and ground planes and 2-ounce copper traces on top and bottom layers with approximately 80% copper coverage. No airflow and no heat sink applied (reference EIA/JEDEC 51.7). It also does not account for other heat sources that may be present on the PCB next to the device in question (such as inductors, resistors etc.)
2. The maximum power dissipation (P_D) is dependent on input voltage, output voltage, output current, external components selected, and PCB layout. The reference data is obtained based on $T_{JMAX} = 125^\circ\text{C}$ and $T_A = 25^\circ\text{C}$.
3. Moisture Sensitivity Level (MSL): IPC/JEDEC standard: J-STD-020A.

ELECTRICAL CHARACTERISTICS ($V_{IN} = 12\text{ V}$, typical values are referenced to $T_A = T_J = 25^\circ\text{C}$, Min and Max values are referenced to $T_J = -40^\circ\text{C}$ to 125°C , unless other noted.)

Characteristics	Test Conditions	Symbol	MIN	TYP	MAX	UNITS
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SUPPLY VOLTAGE MONITOR

VCC Under-Voltage (UVLO) Threshold	VCC falling	V_{DDUV-}	4.0			V
VCC OK Threshold	VCC rising	V_{DDOK}			4.4	V
VCC UVLO Hysteresis		V_{DDHYS}		200		mV

SUPPLY CURRENT

PVIN Shutdown Current	EN low	I_{SDPVIN}	–	0.85	6	μA
VIN Quiescent Supply Current (VCC Current Included)	EN high, no switching, $V_{IN} = 18\text{ V}$, $V_{CC} = V_{DRV}$ (Internal LDO supply for VCC)	I_{QVIN}	–	13	18	mA
	EN high, no switching, $V_{IN} = V_{DRV} = V_{CC} = 4.5\text{ V}$ (External 4.5 V supply for VCC)		–	13	20	
VIN Shutdown Current (VCC Current Included)	EN low, $V_{IN} = 18\text{ V}$, $V_{CC} = V_{DRV}$ (Internal LDO supply for VCC)	I_{QCC}	–	30	45	μA
	EN low, $V_{IN} = V_{DRV} = V_{CC} = 4.5\text{ V}$ (External 4.5 V supply for VCC)		–	50	200	

5 V LINEAR REGULATOR

Output Voltage	$6\text{ V} < V_{IN} < 18\text{ V}$, $I_{DRV} = 0$ to 30 mA (External) EN high, no switching	V_{DRV}	4.8	5.0	5.3	V
Dropout Voltage	$V_{IN} = 5\text{ V}$, $I_{DRV} = 50\text{ mA}$ (External), EN high, no switching	V_{DO}			200	mV

PWM MODULATION

Minimum On Time	(Note 4)	T_{on_min}		50		ns
Minimum Off Time	(Note 4)	T_{off_min}		200		ns

REGULATION ACCURACY

System Voltage Accuracy	5 mV VID Step Mode	$1.0\text{ V} \leq \text{DAC} \leq 1.52\text{ V}$		–0.5% *DAC		0.5% *DAC	V
		$0.8\text{ V} \leq \text{DAC} \leq 0.995\text{ V}$		–5 m		+5 m	
		$0.25\text{ V} \leq \text{DAC} \leq 0.795\text{ V}$		–8 m		+8 m	
System Voltage Accuracy	10 mV VID Step Mode	$1.5\text{ V} \leq \text{DAC} \leq 2.0\text{ V}$		–0.5% *DAC		0.5% *DAC	V
		$1.0\text{ V} \leq \text{DAC} \leq 1.49\text{ V}$		–8 m		+8 m	
		$0.5\text{ V} \leq \text{DAC} \leq 0.99\text{ V}$		–10 m		+10 m	

DVID

Fast Slew Rate	Programmed at Mode Pin	FSR		10		mV/ μs
				20		
	Slew Rate Tolerance		0		15	%
Slow Slew Rate		SSR	FSR/2 FSR/4 (default) FSR/8 FSR/16			mV/ μs
	Slew Rate Tolerance		0		15	

ELECTRICAL CHARACTERISTICS ($V_{IN} = 12\text{ V}$, typical values are referenced to $T_A = T_J = 25^\circ\text{C}$, Min and Max values are referenced to $T_J = -40^\circ\text{C}$ to 125°C , unless other noted.)

Characteristics	Test Conditions	Symbol	MIN	TYP	MAX	UNITS
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CURRENT-SENSE AMPLIFIER

Closed-Loop DC Gain		$GAIN_{CA}$		-12		V/V
-3dB Gain Bandwidth	(Note 4)	BW_{CA}		10		MHz
Input Offset Voltage	$V_{osCS} = V_{SW} - V_{PGND}$ (Note 4)	V_{osCS}	-500	-	500	μV

ENABLE

EN ON Threshold		V_{EN_TH}	0.69	0.8	0.88	V
Hysteresis Resistance		R_{HYS}		40		$k\Omega$
Hysteresis Current		I_{EN_HYS}		5		μA
EN Pin Operating Voltage		V_{EN}	0		3.0	V
EN Input Leakage Current	EN = 0 V	I_{EN_LK}			1.0	μA

SWITCHING FREQUENCY

Switching Frequency in CCM (Note 4)	Programmed at Mode Pin	F_{SW}		1000		kHz
				800		
				600		
	Programmed at Addr Pin			400		
Source Current from Mode Pin		I_{FSET}	48.5	50	51.5	μA

SOFT START

System Reset Time	VCC = 5 V, measured from EN to start of soft start	T_{RST}	0.7	1.0	1.3	ms
Soft Start Slew Rate		SSSR		FSR/4		mV/ μs

PGOOD

PGOOD Startup Delay	Measured from end of Soft Start to PGOOD assertion	T_{d_PGOOD}			6	μs
PGOOD Shutdown Delay	Measured from EN to PGOOD de-assertion			5		ns
PGOOD Low Voltage	$I_{PGOOD} = -4\text{ mA}$	V_{IPGOOD}			0.3	V
PGOOD Leakage Current	PGOOD = 5 V	$I_{lkPGOOD}$			1.0	μA

PROTECTIONS

Valley Current Limit Threshold (Note 4)	$T_A = T_J = 25^\circ\text{C}$	$R_{LIM} = 52.3\text{ k}\Omega$	I_{LMT_Valley}		50		A
		$R_{LIM} = 47.5\text{ k}\Omega$			45		
		$R_{LIM} = 42.2\text{ k}\Omega$			40		
		$R_{LIM} = 36.5\text{ k}\Omega$			35		
		$R_{LIM} = 31.6\text{ k}\Omega$			30		
		$R_{LIM} = 26.1\text{ k}\Omega$			25		
		$R_{LIM} = 21.0\text{ k}\Omega$			20		
		$R_{LIM} = 15.4\text{ k}\Omega$			15		
		$R_{LIM} = 10.2\text{ k}\Omega$			10		
Fast Under Voltage Protection (FUV) Threshold	FB to AGND			0.15	0.2	0.25	V
Fast Under Voltage Protection (FUV) Delay	(Note 4)				1.0		μs
Slow Under Voltage Protection (SUV) Threshold	COMP to AGND (Note 4)				3.0		V
Slow Under Voltage Protection (SUV) Delay	(Note 4)				50		μs

ELECTRICAL CHARACTERISTICS ($V_{IN} = 12\text{ V}$, typical values are referenced to $T_A = T_J = 25^\circ\text{C}$, Min and Max values are referenced to $T_J = -40^\circ\text{C}$ to 125°C , unless other noted.)

Characteristics	Test Conditions	Symbol	MIN	TYP	MAX	UNITS
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PROTECTIONS

Absolute Over Voltage Threshold During Soft-Start	FB to AGND		1.92	2.0	2.08	V
Absolute Over Voltage Threshold Hysteresis	(Note 4)			-25		mV
Over Voltage Threshold Above DAC	FB rising	V_{OVTH}	165	200	235	mV
Over Voltage Debounce Time	FB rising to GL high			1.0		μs
Thermal Shutdown (TSD) Threshold	(Note 4)	T_{sd}	140	150		$^\circ\text{C}$
Recovery Temperature Threshold	(Note 4)	T_{rec}		125		$^\circ\text{C}$
Thermal Shutdown (TSD) Debounce Time	(Note 4)			125		ns

TEMPERATURE TELEMETRY

Temperature Telemetry Tolerance	$T_A = T_J = 90\sim 120^\circ\text{C}$ (Note 4)		-4.0		+4.0	$^\circ\text{C}$
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VBOOT

Sensing Current			9.7	10	10.3	μA
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ADDRESS

Sensing Current			9.7	10	10.3	μA
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IMAX

Sensing Current			12.125	12.5	12.875	μA
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CLK, DATA

Input High Voltage		V_{IH}	0.65			V
Input Low Voltage		V_{IL}			0.45	V
Input Threshold Hysteresis		V_{HYS}		50		mV
Buffer On Resistance (Data)		R_{ON}	4		13	Ω
Input Leakage Current	Pin voltage between 0 and 1.05 V		-100		100	μA
Input Capacitance	(Note 4)				4.0	pF
VR Clock to Data Delay	Time between Clk rising edge and valid Data level (Note 4)	T_{co}	4		8.3	ns
Setup Time	Time before Clk falling (sampling) edge that Data level must be valid (Note 4)	T_{su}	7			ns
Hold Time	Time after Clk falling edge that the Data level remains valid (Note 4)	T_{hld}	14			ns

ALERT#

Output On Resistance		R_{ON}	4		13	Ω
Output Leakage Current	High Impedance State, ALERT # = 3.3 V		-1.0	-	1.0	μA

ADC

Voltage Range	(Note 4)		0		2.0	V
Total Unadjusted Error (TUE)	(Note 4)		-1		1	%
Differential Nonlinearity (DNL)	8-bit (Note 4)				1	LSB
Power Supply Sensitivity	(Note 4)			+/-1		%
Conversion Time	(Note 4)			30		μs
Round Robin	(Note 4)			90		μs

4. Guaranteed by design and/or characterization, not tested in production.

TYPICAL CHARACTERISTICS

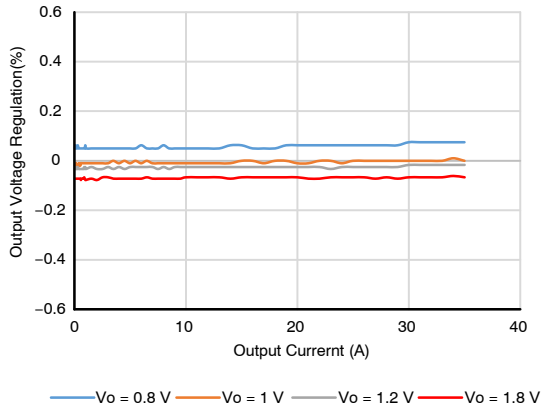


Figure 4. NCP3285AF FCCM Load Regulation

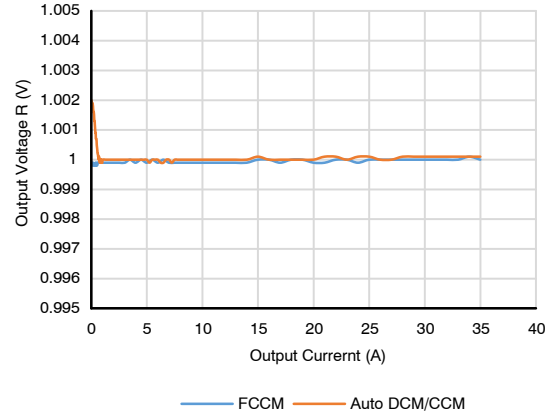


Figure 5. NCP3285AF Output Voltage vs Output Current

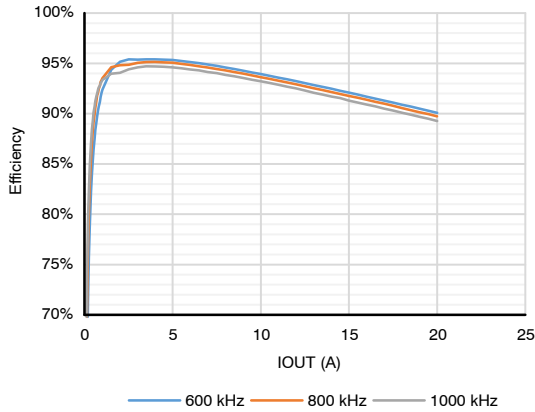


Figure 6. NCP3285F Efficiency vs Output Current
($V_{IN} = 5\text{ V}$, $V_{OUT} = 1\text{ V}$, FCCM)

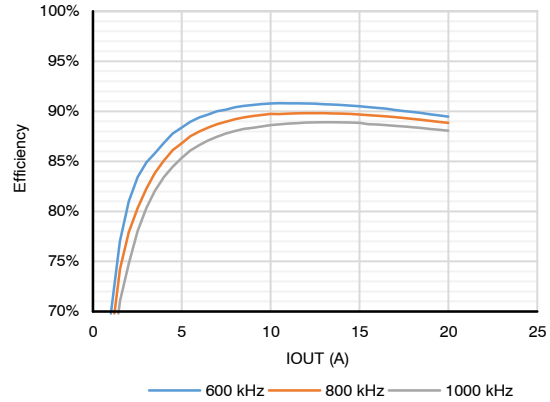


Figure 7. NCP3285F Efficiency vs Output Current
($V_{IN} = 12\text{ V}$, $V_{OUT} = 1\text{ V}$, FCCM)

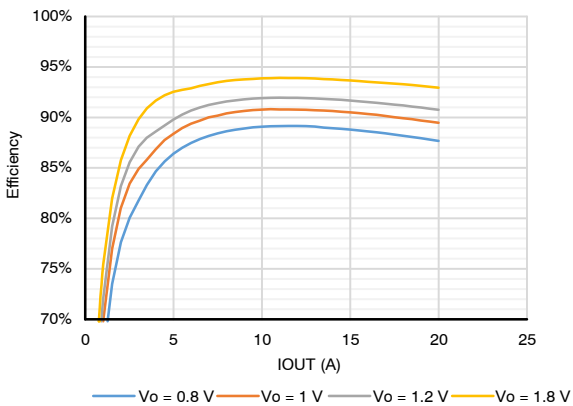


Figure 8. NCP3285F Efficiency vs Output Current
($V_{IN} = 12\text{ V}$, $F_{sw} = 600\text{ kHz}$, FCCM)

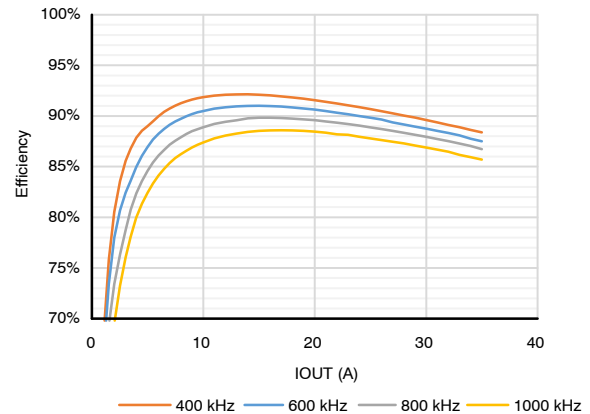


Figure 9. NCP3285AF Efficiency vs Output Current
($V_{IN} = 12\text{ V}$, $V_{OUT} = 1\text{ V}$, FCCM)

TYPICAL CHARACTERISTICS (continued)

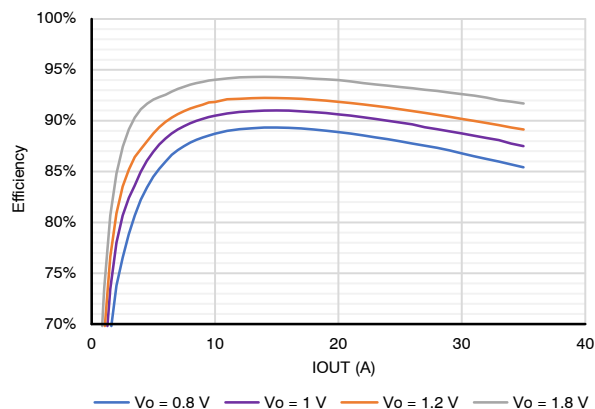


Figure 10. NCP3285AF Efficiency vs Output Current
($V_{IN} = 12\text{ V}$, $f_{SW} = 600\text{ kHz}$, FCCM)

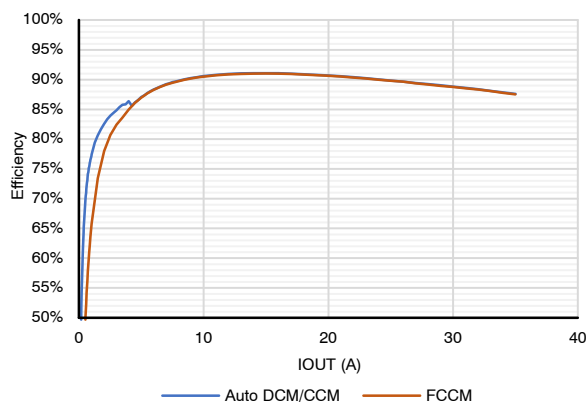
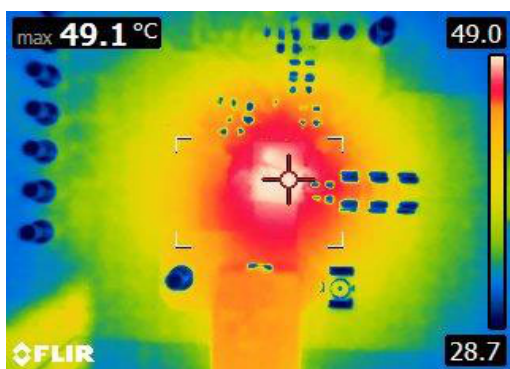
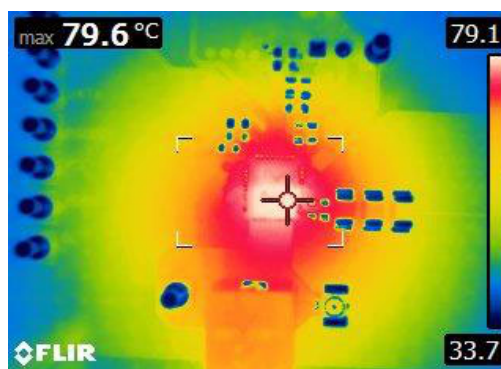


Figure 11. NCP3285AF Efficiency vs Output Current
($V_{IN} = 12\text{ V}$, $V_{OUT} = 1\text{ V}$, $f_{SW} = 600\text{ kHz}$)



NCP3285F EVB $V_{IN} = 12\text{ V}$ $V_o = 1\text{ V}$ $I_{OUT} = 20\text{ A}$ $f_{SW} = 600\text{ kHz}$
 $T_A = 23^\circ\text{C}$ No Airflow

Figure 12. Thermal Image



NCP3285AF EVB $V_{IN} = 12\text{ V}$ $V_o = 1\text{ V}$ $I_{OUT} = 35\text{ A}$ $f_{SW} = 600\text{ kHz}$
 $T_A = 23^\circ\text{C}$ No Airflow

Figure 13. Thermal Image

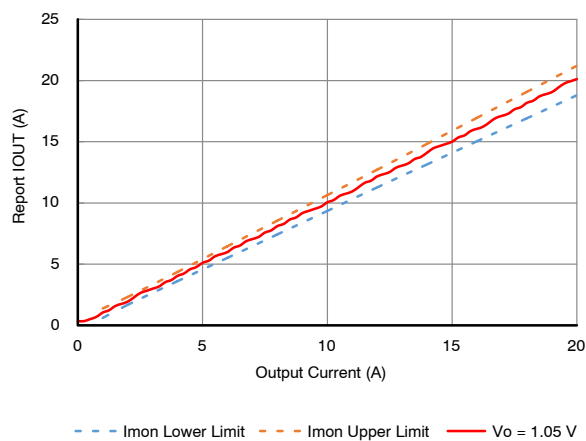


Figure 14. NCP3285F I_{OUT} Report vs Output Current
($V_{IN} = 12\text{ V}$, $V_{OUT} = 1.05\text{ V}$)

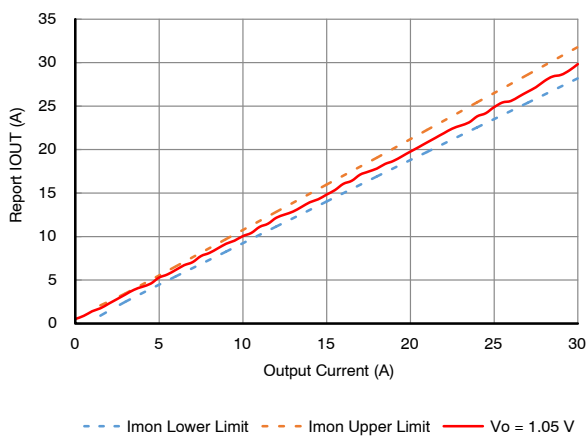


Figure 15. NCP3285AF I_{OUT} Report vs Output Current
($V_{IN} = 12\text{ V}$, $V_{OUT} = 1.05\text{ V}$)

Table 1. VR13 & VR14 VID CODES

VID7	VID6	VID5	VID4	VID3	VID2	VID1	VID0	Voltage (V)		HEX
								5 mV Mode	10 mV Mode	
0	0	0	0	0	0	0	0	0.000	0.000	00
0	0	0	0	0	0	0	1	0.250	0.500	01
0	0	0	0	0	0	1	0	0.255	0.510	02
0	0	0	0	0	0	1	1	0.260	0.520	03
0	0	0	0	0	1	0	0	0.265	0.530	04
0	0	0	0	0	1	0	1	0.270	0.540	05
0	0	0	0	0	1	1	0	0.275	0.550	06
0	0	0	0	0	1	1	1	0.280	0.560	07
0	0	0	0	1	0	0	0	0.285	0.570	08
0	0	0	0	1	0	0	1	0.290	0.580	09
0	0	0	0	1	0	1	0	0.295	0.590	0A
0	0	0	0	1	0	1	1	0.300	0.600	0B
0	0	0	0	1	1	0	0	0.305	0.610	0C
0	0	0	0	1	1	0	1	0.310	0.620	0D
0	0	0	0	1	1	1	0	0.315	0.630	0E
0	0	0	0	1	1	1	1	0.320	0.640	0F
0	0	0	1	0	0	0	0	0.325	0.650	10
0	0	0	1	0	0	0	1	0.330	0.660	11
0	0	0	1	0	0	1	0	0.335	0.670	12
0	0	0	1	0	0	1	1	0.340	0.680	13
0	0	0	1	0	1	0	0	0.345	0.690	14
0	0	0	1	0	1	0	1	0.350	0.700	15
0	0	0	1	0	1	1	0	0.355	0.710	16
0	0	0	1	0	1	1	1	0.360	0.720	17
0	0	0	1	1	0	0	0	0.365	0.730	18
0	0	0	1	1	0	0	1	0.370	0.740	19
0	0	0	1	1	0	1	0	0.375	0.750	1A
0	0	0	1	1	0	1	1	0.380	0.760	1B
0	0	0	1	1	1	0	0	0.385	0.770	1C
0	0	0	1	1	1	0	1	0.390	0.780	1D
0	0	0	1	1	1	1	0	0.395	0.790	1E
0	0	0	1	1	1	1	1	0.400	0.800	1F
0	0	1	0	0	0	0	0	0.405	0.810	20
0	0	1	0	0	0	0	1	0.410	0.820	21
0	0	1	0	0	0	1	0	0.415	0.830	22
0	0	1	0	0	0	1	1	0.420	0.840	23
0	0	1	0	0	1	0	0	0.425	0.850	24
0	0	1	0	0	1	0	1	0.430	0.860	25
0	0	1	0	0	1	1	0	0.435	0.870	26
0	0	1	0	0	1	1	1	0.440	0.880	27

Table 1. VR13 & VR14 VID CODES

VID7	VID6	VID5	VID4	VID3	VID2	VID1	VID0	Voltage (V)		HEX
								5 mV Mode	10 mV Mode	
0	0	1	0	1	0	0	0	0.445	0.890	28
0	0	1	0	1	0	0	1	0.450	0.900	29
0	0	1	0	1	0	1	0	0.455	0.910	2A
0	0	1	0	1	0	1	1	0.460	0.920	2B
0	0	1	0	1	1	0	0	0.465	0.930	2C
0	0	1	0	1	1	0	1	0.470	0.940	2D
0	0	1	0	1	1	1	0	0.475	0.950	2E
0	0	1	0	1	1	1	1	0.480	0.960	2F
0	0	1	1	0	0	0	0	0.485	0.970	30
0	0	1	1	0	0	0	1	0.490	0.980	31
0	0	1	1	0	0	1	0	0.495	0.990	32
0	0	1	1	0	0	1	1	0.500	1.000	33
0	0	1	1	0	1	0	0	0.505	1.010	34
0	0	1	1	0	1	0	1	0.510	1.020	35
0	0	1	1	0	1	1	0	0.515	1.030	36
0	0	1	1	0	1	1	1	0.520	1.040	37
0	0	1	1	1	0	0	0	0.525	1.050	38
0	0	1	1	1	0	0	1	0.530	1.060	39
0	0	1	1	1	0	1	0	0.535	1.070	3A
0	0	1	1	1	0	1	1	0.540	1.080	3B
0	0	1	1	1	1	0	0	0.545	1.090	3C
0	0	1	1	1	1	0	1	0.550	1.100	3D
0	0	1	1	1	1	1	0	0.555	1.110	3E
0	0	1	1	1	1	1	1	0.560	1.120	3F
0	1	0	0	0	0	0	0	0.565	1.130	40
0	1	0	0	0	0	0	1	0.570	1.140	41
0	1	0	0	0	0	1	0	0.575	1.150	42
0	1	0	0	0	0	1	1	0.580	1.160	43
0	1	0	0	0	1	0	0	0.585	1.170	44
0	1	0	0	0	1	0	1	0.590	1.180	45
0	1	0	0	0	1	1	0	0.595	1.190	46
0	1	0	0	0	1	1	1	0.600	1.200	47
0	1	0	0	1	0	0	0	0.605	1.210	48
0	1	0	0	1	0	0	1	0.610	1.220	49
0	1	0	0	1	0	1	0	0.615	1.230	4A
0	1	0	0	1	0	1	1	0.620	1.240	4B
0	1	0	0	1	1	0	0	0.625	1.250	4C
0	1	0	0	1	1	0	1	0.630	1.260	4D
0	1	0	0	1	1	1	0	0.635	1.270	4E
0	1	0	0	1	1	1	1	0.640	1.280	4F

Table 1. VR13 & VR14 VID CODES

VID7	VID6	VID5	VID4	VID3	VID2	VID1	VID0	Voltage (V)		HEX
								5 mV Mode	10 mV Mode	
0	1	0	1	0	0	0	0	0.645	1.290	50
0	1	0	1	0	0	0	1	0.650	1.300	51
0	1	0	1	0	0	1	0	0.655	1.310	52
0	1	0	1	0	0	1	1	0.660	1.320	53
0	1	0	1	0	1	0	0	0.665	1.330	54
0	1	0	1	0	1	0	1	0.670	1.340	55
0	1	0	1	0	1	1	0	0.675	1.350	56
0	1	0	1	0	1	1	1	0.680	1.360	57
0	1	0	1	1	0	0	0	0.685	1.370	58
0	1	0	1	1	0	0	1	0.690	1.380	59
0	1	0	1	1	0	1	0	0.695	1.390	5A
0	1	0	1	1	0	1	1	0.700	1.400	5B
0	1	0	1	1	1	0	0	0.705	1.410	5C
0	1	0	1	1	1	0	1	0.710	1.420	5D
0	1	0	1	1	1	1	0	0.715	1.430	5E
0	1	0	1	1	1	1	1	0.720	1.440	5F
0	1	1	0	0	0	0	0	0.725	1.450	60
0	1	1	0	0	0	0	1	0.730	1.460	61
0	1	1	0	0	0	1	0	0.735	1.470	62
0	1	1	0	0	0	1	1	0.740	1.480	63
0	1	1	0	0	1	0	0	0.745	1.490	64
0	1	1	0	0	1	0	1	0.750	1.500	65
0	1	1	0	0	1	1	0	0.755	1.510	66
0	1	1	0	0	1	1	1	0.760	1.520	67
0	1	1	0	1	0	0	0	0.765	1.530	68
0	1	1	0	1	0	0	1	0.770	1.540	69
0	1	1	0	1	0	1	0	0.775	1.550	6A
0	1	1	0	1	0	1	1	0.780	1.560	6B
0	1	1	0	1	1	0	0	0.785	1.570	6C
0	1	1	0	1	1	0	1	0.790	1.580	6D
0	1	1	0	1	1	1	0	0.795	1.590	6E
0	1	1	0	1	1	1	1	0.800	1.600	6F
0	1	1	1	0	0	0	0	0.805	1.610	70
0	1	1	1	0	0	0	1	0.810	1.620	71
0	1	1	1	0	0	1	0	0.815	1.630	72
0	1	1	1	0	0	1	1	0.820	1.640	73
0	1	1	1	0	1	0	0	0.825	1.650	74
0	1	1	1	0	1	0	1	0.830	1.660	75
0	1	1	1	0	1	1	0	0.835	1.670	76
0	1	1	1	0	1	1	1	0.840	1.680	77

Table 1. VR13 & VR14 VID CODES

VID7	VID6	VID5	VID4	VID3	VID2	VID1	VID0	Voltage (V)		HEX
								5 mV Mode	10 mV Mode	
0	1	1	1	1	0	0	0	0.845	1.690	78
0	1	1	1	1	0	0	1	0.850	1.700	79
0	1	1	1	1	0	1	0	0.855	1.710	7A
0	1	1	1	1	0	1	1	0.860	1.720	7B
0	1	1	1	1	1	0	0	0.865	1.730	7C
0	1	1	1	1	1	0	1	0.870	1.740	7D
0	1	1	1	1	1	1	0	0.875	1.750	7E
0	1	1	1	1	1	1	1	0.880	1.760	7F
1	0	0	0	0	0	0	0	0.885	1.770	80
1	0	0	0	0	0	0	1	0.890	1.780	81
1	0	0	0	0	0	1	0	0.895	1.790	82
1	0	0	0	0	0	1	1	0.900	1.800	83
1	0	0	0	0	1	0	0	0.905	1.810	84
1	0	0	0	0	1	0	1	0.910	1.820	85
1	0	0	0	0	1	1	0	0.915	1.830	86
1	0	0	0	0	1	1	1	0.920	1.840	87
1	0	0	0	1	0	0	0	0.925	1.850	88
1	0	0	0	1	0	0	1	0.930	1.860	89
1	0	0	0	1	0	1	0	0.935	1.870	8A
1	0	0	0	1	0	1	1	0.940	1.880	8B
1	0	0	0	1	1	0	0	0.945	1.890	8C
1	0	0	0	1	1	0	1	0.950	1.900	8D
1	0	0	0	1	1	1	0	0.955	1.910	8E
1	0	0	0	1	1	1	1	0.960	1.920	8F
1	0	0	1	0	0	0	0	0.965	1.930	90
1	0	0	1	0	0	0	1	0.970	1.940	91
1	0	0	1	0	0	1	0	0.975	1.950	92
1	0	0	1	0	0	1	1	0.980	1.960	93
1	0	0	1	0	1	0	0	0.985	1.970	94
1	0	0	1	0	1	0	1	0.990	1.980	95
1	0	0	1	0	1	1	0	0.995	1.990	96
1	0	0	1	0	1	1	1	1.000	2.000	97
1	0	0	1	1	0	0	0	1.005	2.010	98
1	0	0	1	1	0	0	1	1.010	2.020	99
1	0	0	1	1	0	1	0	1.015	2.030	9A
1	0	0	1	1	0	1	1	1.020	2.040	9B
1	0	0	1	1	1	0	0	1.025	2.050	9C
1	0	0	1	1	1	0	1	1.030	2.060	9D
1	0	0	1	1	1	1	0	1.035	2.070	9E
1	0	0	1	1	1	1	1	1.040	2.080	9F

Table 1. VR13 & VR14 VID CODES

VID7	VID6	VID5	VID4	VID3	VID2	VID1	VID0	Voltage (V)		HEX
								5 mV Mode	10 mV Mode	
1	0	1	0	0	0	0	0	1.045	2.090	A0
1	0	1	0	0	0	0	1	1.050	2.100	A1
1	0	1	0	0	0	1	0	1.055	2.110	A2
1	0	1	0	0	0	1	1	1.060	2.120	A3
1	0	1	0	0	1	0	0	1.065	2.130	A4
1	0	1	0	0	1	0	1	1.070	2.140	A5
1	0	1	0	0	1	1	0	1.075	2.150	A6
1	0	1	0	0	1	1	1	1.080	2.160	A7
1	0	1	0	1	0	0	0	1.085	2.170	A8
1	0	1	0	1	0	0	1	1.090	2.180	A9
1	0	1	0	1	0	1	0	1.095	2.190	AA
1	0	1	0	1	0	1	1	1.100	2.200	AB
1	0	1	0	1	1	0	0	1.105	2.210	AC
1	0	1	0	1	1	0	1	1.110	2.220	AD
1	0	1	0	1	1	1	0	1.115	2.230	AE
1	0	1	0	1	1	1	1	1.120	2.240	AF
1	0	1	1	0	0	0	0	1.125	2.250	B0
1	0	1	1	0	0	0	1	1.130	2.260	B1
1	0	1	1	0	0	1	0	1.135	2.270	B2
1	0	1	1	0	0	1	1	1.140	2.280	B3
1	0	1	1	0	1	0	0	1.145	2.290	B4
1	0	1	1	0	1	0	1	1.150	2.300	B5
1	0	1	1	0	1	1	0	1.155	2.310	B6
1	0	1	1	0	1	1	1	1.160	2.320	B7
1	0	1	1	1	0	0	0	1.165	2.330	B8
1	0	1	1	1	0	0	1	1.170	2.340	B9
1	0	1	1	1	0	1	0	1.175	2.350	BA
1	0	1	1	1	0	1	1	1.180	2.360	BB
1	0	1	1	1	1	0	0	1.185	2.370	BC
1	0	1	1	1	1	0	1	1.190	2.380	BD
1	0	1	1	1	1	1	0	1.195	2.390	BE
1	0	1	1	1	1	1	1	1.200	2.400	BF
1	1	0	0	0	0	0	0	1.205	2.410	C0
1	1	0	0	0	0	0	1	1.210	2.420	C1
1	1	0	0	0	0	1	0	1.215	2.430	C2
1	1	0	0	0	0	1	1	1.220	2.440	C3
1	1	0	0	0	1	0	0	1.225	2.450	C4
1	1	0	0	0	1	0	1	1.230	2.460	C5
1	1	0	0	0	1	1	0	1.235	2.470	C6
1	1	0	0	0	1	1	1	1.240	2.480	C7

Table 1. VR13 & VR14 VID CODES

VID7	VID6	VID5	VID4	VID3	VID2	VID1	VID0	Voltage (V)		HEX
								5 mV Mode	10 mV Mode	
1	1	0	0	1	0	0	0	1.245	2.490	C8
1	1	0	0	1	0	0	1	1.250	2.500	C9
1	1	0	0	1	0	1	0	1.255	2.510	CA
1	1	0	0	1	0	1	1	1.260	2.520	CB
1	1	0	0	1	1	0	0	1.265	2.530	CC
1	1	0	0	1	1	0	1	1.270	2.540	CD
1	1	0	0	1	1	1	0	1.275	2.550	CE
1	1	0	0	1	1	1	1	1.280	2.560	CF
1	1	0	1	0	0	0	0	1.285	2.570	D0
1	1	0	1	0	0	0	1	1.290	2.580	D1
1	1	0	1	0	0	1	0	1.295	2.590	D2
1	1	0	1	0	0	1	1	1.300	2.600	D3
1	1	0	1	0	1	0	0	1.305	2.610	D4
1	1	0	1	0	1	0	1	1.310	2.620	D5
1	1	0	1	0	1	1	0	1.315	2.630	D6
1	1	0	1	0	1	1	1	1.320	2.640	D7
1	1	0	1	1	0	0	0	1.325	2.650	D8
1	1	0	1	1	0	0	1	1.330	2.660	D9
1	1	0	1	1	0	1	0	1.335	2.670	DA
1	1	0	1	1	0	1	1	1.340	2.680	DB
1	1	0	1	1	1	0	0	1.345	2.690	DC
1	1	0	1	1	1	0	1	1.350	2.700	DD
1	1	0	1	1	1	1	0	1.355	2.710	DE
1	1	0	1	1	1	1	1	1.360	2.720	DF
1	1	1	0	0	0	0	0	1.365	2.730	E0
1	1	1	0	0	0	0	1	1.370	2.740	E1
1	1	1	0	0	0	1	0	1.375	2.750	E2
1	1	1	0	0	0	1	1	1.380	2.760	E3
1	1	1	0	0	1	0	0	1.385	2.770	E4
1	1	1	0	0	1	0	1	1.390	2.780	E5
1	1	1	0	0	1	1	0	1.395	2.790	E6
1	1	1	0	0	1	1	1	1.400	2.800	E7
1	1	1	0	1	0	0	0	1.405	2.810	E8
1	1	1	0	1	0	0	1	1.410	2.820	E9
1	1	1	0	1	0	1	0	1.415	2.830	EA
1	1	1	0	1	0	1	1	1.420	2.840	EB
1	1	1	0	1	1	0	0	1.425	2.850	EC
1	1	1	0	1	1	0	1	1.430	2.860	ED
1	1	1	0	1	1	1	0	1.435	2.870	EE
1	1	1	0	1	1	1	1	1.440	2.880	EF

Table 1. VR13 & VR14 VID CODES

VID7	VID6	VID5	VID4	VID3	VID2	VID1	VID0	Voltage (V)		HEX
								5 mV Mode	10 mV Mode	
1	1	1	1	0	0	0	0	1.445	2.890	F0
1	1	1	1	0	0	0	1	1.450	2.900	F1
1	1	1	1	0	0	1	0	1.455	2.910	F2
1	1	1	1	0	0	1	1	1.460	2.920	F3
1	1	1	1	0	1	0	0	1.465	2.930	F4
1	1	1	1	0	1	0	1	1.470	2.940	F5
1	1	1	1	0	1	1	0	1.475	2.950	F6
1	1	1	1	0	1	1	1	1.480	2.960	F7
1	1	1	1	1	0	0	0	1.485	2.970	F8
1	1	1	1	1	0	0	1	1.490	2.980	F9
1	1	1	1	1	0	1	0	1.495	2.990	FA
1	1	1	1	1	0	1	1	1.500	3.000	FB
1	1	1	1	1	1	0	0	1.505	3.010	FC
1	1	1	1	1	1	0	1	1.510	3.020	FD
1	1	1	1	1	1	1	0	1.515	3.030	FE
1	1	1	1	1	1	1	1	1.520	3.040	FF

Table 2. SUPPORTED SVID COMMANDS

#	Command	Master Payload	Slave Payload	Description
01h	SetVID_Fast	VID Code	N/A	Set the new VID target, VR Jumps to new VID target with controlled (up or down) slew rate programmed by the VR
02h	SetVID_Slow	VID Code	N/A	Set the VID target, VR jumps to new VID target with controlled slew rate (up or down) programmed by the VR
03h	SetVID_Decay	VID Code	N/A	Sets the VID target, VR jumps to new VID target, but does not control the slew rate, the output voltage decays at a rate proportional to the load current. SetVID_Decay is only used in VID down direction
04h	SetPS	Byte indicating power state for slave	N/A	Sends information to VR controller so it can configure VR to improve efficiency, especially at light load
05h	SetRegAddr	Address of the index in the data table	N/A	Sets the address pointer in the data register table. Typically the next command SetRegData is the payload that gets loaded into this address
06h	SetRegData	New data register contents	N/A	Writes the contents to the data register that was previously identified by the address pointer with SetRegAddr
07h	GetReg	Register Address	Specified register contents	Slave returns the contents of the specified register as the payload; The majority of the VR monitoring data is accessed through the GetReg command
08h	Test Mode			For evaluation purpose only
09h	SetWP	Byte indicating the working point, slew rate, and alert to select.	N/A	SetWP payload is a bit mapped word that identifies the WP registers which hold the new target VID code, transition slew rate, and alert# behavior when the voltage rails transition to the new voltage targets

Table 3. SUPPORTED SVID REGISTERS

Index	Name	Description	Master Access	Default
00h	Vendor ID	Uniquely identifies the VR vendor. The vendor ID assigned by Intel to ON Semiconductor is 0x1Ah	R	1Ah
01h	Product ID	Uniquely identifies the VR product. The VR vendor assigns this number	R	5Fh
02h	Product Revision	Uniquely identifies the revision or stepping of the VR control IC	R	00h
03h	Date code ID		R	00h
05h	Protocol ID	Identifies the SVID protocol the controller supports: 04h = VR13 and 10 mV VID, 07h = VR13 and 5 mV VID; 09h = VR14 and 5 mV VID, 0Ah = VR14 and 10 mV VID	R	04h/07h or 09h/0Ah
06h	Capability	Informs the Master of the controller's Capabilities, 1 = supported, 0 = not supported Bit 7 = Iout_format. Bit 7 = 0 when 1A = 1LSB of Reg 15h. Bit 7 = 1 when Reg 15 FFh = Icc_Max. Default = 1 Bit 6 = ADC Measurement of Temp Supported = 1 Bit 5 = ADC Measurement of Pin Supported = 0 Bit 4 = ADC Measurement of Vin Supported = 0 Bit 3 = ADC Measurement of Iin Supported = 0 Bit 2 = ADC Measurement of Pout Supported = 0 Bit 1 = ADC Measurement of Vout Supported = 0 Bit 0 = ADC Measurement of Iout Supported = 1	R	C1h
09h	VIDOMax_H_Capa	Bit [7:1]: Reserved, set to 0 Bit [0]: MSBit of the 9-bit maximum effective VID(VID+OFFSET);	R	01h
0Ah	VIDOMax_L	LSByte of the 9-bit maximum effective VID (VID+OFFSET)	R	7Eh
0Fh	Allcall_act	Controls which All-Call rails are active: Bit [7:2]: Reserved, set to 0 Bit [1]: 1 = Slave device responds to all-call slave addr 0xE 0 = Slave device rejects all-calls slave addr 0xE Bit [0]: 1 = Slave device responds to all-call slave addr 0xF 0 = Slave device rejects all-call slave addr 0xF	R/W	01h
10h	Status_1	Data register read after ALERT# signal is asserted. Conveying the status of the VR. (pp.113, Intel #456098 rev.1.92)	R	00h
11h	Status_2	Data register showing optional status_2 data. (pp.114, Intel #456098, rev 1.92)	R	00h
12h	Temp Zone	Data register showing temperature zones the system is operating in. (pp.130, Intel #456098, rev 1.92) 1 tick is 3°C	R	00h
14h	Last read	Contains last value read by GET_REG command	R	00h
15h	I_out	8 bit binary word ADC of current. The ADC should be scaled such that Ffh = IMAX for the VR for maximum resolution of the ADC data	R	00h
16h	V_out	Not supported	R	00h
17h	VR_Temp	8 bit binary word ADC of temperature. Binary format in °C, i.e. 64h = 100°C. 00h indicates this function is not supported. Default value of 19h means 25°C	R	19h
18h	P_out	Not supported	R	
1Bh	PIN_H	Not supported	R	
1Ch	Status 2 Last read	When the status 2 register is read its contents are copied into this register. The format is the same as the Status 2 Register	R	00h
1Eh	CFG_FILE_ID	Configuration File Version Identifier	R	00h
21h	Icc_Max	Data register containing the Icc_Max. 1 LSB means 1 A. Default value 19h = 25 A.	R	19h
22h	Temp_Max	Data register containing the max temperature and the level VR_hot asserts. This value defaults to 100°C.	R	64h
23h	DC_LL	Programmed Load Line, set to 0 (No load line)	R	00h

Table 3. SUPPORTED SVID REGISTERS

Index	Name	Description	Master Access	Default
24h	SR_fast	Slew Rate for SetVID_fast commands. Binary format in mV/μs.	R	0Ah
25h	SR_slow	Slew Rate for SetVID_slow commands. It is 4X slower than the SR_fast rate. Binary format in mV/μs	R	02h
26h	Vboot	The NCP3285F/AF ramps to Vboot and hold at Vboot until it receives a new SVID SetVID command to move to a different voltage. Default value = 0 V.	R	00h
2Ah	SR_Slow Selector	01h = Fast_SR/2 02h = Fast_SR/4 (Default) 04h = Fast_SR/8 08h = Fast_SR/16	R/W	02h
2Bh	PS4_exit_lat	PS4 exit latency	R	00h
2Ch	PS3_exit_lat	PS3 exit latency	R	00h
2Dh	EN_SVID_RDY_T	Enable to SVID Ready latency, Latency calculation: Time = $x \times 2^{(y-4)}$, where x = 4 bit lower nibble and y = 4 bit upper nibble	R	BAh
2Eh	Pin_Max	Not supported	R	
2Fh	Pin_Alert_TH	Not supported	R	
30h	Vout_Max	Programmed by master and sets the maximum VID the VR will support. If a higher VID code is received, the VR should respond with “Reject” acknowledge. Default values are FBh in 5mV mode and 97h (2.0 V) in 10 mV mode	R/W	FBh/97h
31h	VID setting	Data register containing currently programmed VID voltage. VID data format.	R	00h
32h	Pwr State	Register containing the current programmed power state.	R/W	00h
33h	Offset	Sets offset in VID steps added to the VID setting for voltage margining. Bit 7 is sign bit, 0 = positive margin, 1 = negative margin. Remaining 7 BITS are # VID steps for margin 2's complement. 00h = no offset 01h = +1 VID step 02h = +2 VID steps FFh = -1 VID step FEh = -2 VID steps	R/W	00h
34h	MultiVR Config	VR_Ready_0 V = 1; The VR_Ready line does not de-assert when issued a SetVID(0.0 V) or SetPS(4) command	R/W	01h
36h	DC_LL_Fine	Programmed Load line fine adjustment, set to 0 (No load line)	R	00h
3Ah	Work Point 0	VID target for WP0 command	R/W	00h
3Bh	Work Point 1	VID target for WP1 command	R/W	00h
3Ch	Work Point 2	VID target for WP2 command	R/W	00h
3Dh	Work Point 3	VID target for WP3 command	R/W	00h
50h	High_PWR	High Power Scaling Control: unscaled by default	R	00h
51h	PWRstate_SUP	Indicates Supported Power States: Bit [7:4]: Index of max. supported power state Bit [3]: 1 = If PS4 supported, 0 = not supported Bit [2]: 1 = If PS3 supported, 0 = not supported Bit [1]: 1 = If PS2 supported, 0 = not supported Bit [0]: 1 = If PS1 supported, 0 = not supported	R	23h
52h	PHshed_SUP	Phase Shedding Supported Methods: Auto phase shedding	R	05h
53h	PHshed_ACT	Phase Shedding Active Method : Auto Phase shedding	RW	00h

Table 3. SUPPORTED SVID REGISTERS

Index	Name	Description	Master Access	Default
54h	NegVREN_SUP	VR_EN Negative Edge Behavior Support: Bit [7:5]: Reserved, set to 0 Bit [4]: 1 = If PMBus can be used to select response to VR_EN negative edge is supported, 0 = not supported Bit [3]: 1 = If Other method to 0 V supported as response to VR_EN negative edge, 0 = not supported Bit [2]: 1 = If Fast slew rate to 0 V supported as response to VR_EN negative edge, 0 = not supported Bit [1]: 1 = If Slow slew rate to 0 V supported as response to VR_EN negative edge, 0 = not supported Bit [0]: 1 = If Decay to 0 V supported as response to VR_EN negative edge, 0 = not supported	R	01h
55h	NegVREN_ACT	VR_EN Negative Edge Active Response: Bit [7:3]: Reserved, set to 0 Bit [2:0]: This specifies the slew rate in response to VR_EN negative edge. 000 = Decay (Typical Default) 001 = Slow 010 = Fast 011 = Other method 100 = Controlled via PMBus else = Reserved	R/W	00h
56h	DIGOUT_Status	Digital Output Pin Status: Enable VR_READY active high assertion by default	R	0Fh
57h	WP_Slew_0	WP0 and WP1 Slew Rate & Alert Table Cfg(pp143, Intel #456098 rev.1.92)	R/W	99h
58h	WP_Slew_1	WP2 and WP3 Slew Rate & Alert Table Cfg(pp143, Intel #456098 rev.1.92)	R/W	99h
5Bh	WP_Slew_TT	SetWP Slew Rate Request Translation Table(pp145, Intel #456098 rev.1.92)	R/W	1Bh/5Bh

DETAILED DESCRIPTION

General

The NCP3285F/AF, a single-phase synchronous buck regulator with SVID, integrates power MOSFETs to provide a high-efficiency and compact-footprint power management solution. The NCP3285F/AF is able to deliver up to 20 A / 35 A TDC output current on a wide output voltage range. Operating in high switching frequency up to 1MHz allows employing small size inductors and capacitors while maintaining high efficiency due to integrated solution

with high performance power MOSFETs. It provides differential voltage sense and comprehensive protections.

Operation Modes

Operation mode, switching frequency, VID mode, and fast DVID slew rate are programmed at Mode pin with a $\pm 1\%$ tolerance resistor as shown in Table 4. The 400 kHz switching frequency is also optional, refer to 'SVID Address and Boot-Up Voltage' for more detail information.

Table 4. MODE CONFIGURATION

Resistance @ Mode Pin (Ω, ±1%)	Frequency (kHz)	Operation Mode (PS0 and PS1)	VID Mode		SR_fast		
			VBOOT = 0 V to 1.5 V	VBOOT = 1.6 V to 1.8 V			
0	600	FCCM	5 mV	10 mV	10 mV/μs		
499	800				20 mV/μs		
787	1000						
1.15k	800				10 mV/μs		
1.58k	600						
2.00k	800						
2.49k	1000						
3.16k	800						
3.83k	600	Auto DCM/CCM	10 mV		20 mV/μs		
4.64k	800						
5.62k	1000		5 mV				
6.65k	1000						
7.87k	800		10 mV/μs				
9.09k	600						
10.5k	600		10 mV		20 mV/μs		
12.1k	800						
14.0k	1000				10 mV/μs		
16.2k	1000						
18.7k	800				20 mV/μs		
21.5k	600						
24.9k	600	FCCM	5 mV		10 mV/μs		
28.7k	800						
33.2k	1000						
Float	800						

The NCP3285F/AF may operate in one of three power states, named PS0 (default), PS1, and PS2 as shown in Table 5, which is programmed by SVID SetPS command. The NCP3285F/AF can acknowledge commands of SetPS3

and SetPS4 but actually goes into PS2 mode after receiving those commands. The operation mode in PS0 and PS1 is selected at Mode pin. For VR14 applications, FCCM mode needs to be selected for PS0 and PS1.

Table 5. POWER STATUS AND OPERATION MODES

Power Status	Operation Mode
PS0	Forced CCM or Auto CCM/DCM (by Mode Pin) – normal mode (Default)
PS1	Forced CCM or Auto CCM/DCM (by Mode Pin) – low power mode
PS2	Auto CCM/DCM –very low power mode

To have a consistent mode-change behavior and eliminate possible gate driver failures in response to SVID SetPS command, an internal mode-change synchronization circuit is employed. After receipt of SetPS command, the internal mode-change signal is triggered at either a rising edge of PWM signal or a time-out signal on a first-come first-served basis. The time-out signal is asserted when both high-side and low-side MOSFETs are off for more than 200 ns in DCM operation.

Current-Mode RPM Operation

The NCP3285F/AF operates with the current-mode Ramp-Pulse-Modulation (RPM) scheme in PS0/1/2/3 operation states. In Forced CCM mode, the inductor current is always continuous and the device operates in quasi-fixed switching frequency, which has a typical value programmed by users through a resistor at pin Mode. In Auto CCM/DCM mode, the inductor current is continuous and the device operates in quasi-fixed switching frequency in medium and heavy load range, while the inductor current becomes discontinuous and the device automatically operates in PFM mode with an adaptive fixed on time and variable switching frequency in light load range.

Serial VID interface (SVID)

The NCP3285F/AF supports Intel serial VID interface. It communicates with the microprocessor through three wires (Clk, Data, ALERT#). Clk, Data and ALERT# should be pulled high to CPU I/O voltage VTT (which is typically 1.0 to 1.1 V) using external Resistors. The SVID bus will operate at a frequency up to 43 MHz. For NCP3285F/AF, supported SVID commands are listed in . All the supported registers are shown in Table 3.

SVID Address and Boot-Up Voltage

SVID address is programmed at Addr pin and boot-up voltage is programmed at Vboot pin as shown in Table 6 and Table 7. Need to NOTE that Addr pin could be also used to configure the 400kHz switching frequency, different default value of REG 5Bh and different propocol ID (REG05h), it would override the frequency setting programmed by Mode pin when set to 400 kHz frequency. Refer to below Table 8 for more detail information.

Table 6. SVID ADDRESS SELECTION

Resistance (±1%) @ Addr Pin	SVID Address
88.7k	1011b
75.0k	1010b
61.9k	1001b
51.1k	1000b
43.2k	0111b
36.5k	0110b
30.1k	0101b
21.0k	0100b
14.0k	0011b
9.53k	0010b
5.62k /105k /127k /150k / Float	0001b
0	0000b

Table 7. BOOT-UP VOLTAGE SELECTION

Resistance (±1%) @ Vboot Pin	Boot-Up Voltage (V)
Float	1.8
150k	1.7
127k	1.6
105k	1.5
88.7k	1.35
75.0k	1.25
61.9k	1.2
51.1k	1.1
43.2k	1.05
36.5k	1.0
30.1k	0.95
21.0k	0.9
14.0k	0.85
9.53k	0.8
5.62k	0.75
0	0

Table 8. ADDR PIN EXTENDED CONFIGURATION

Resistance ($\pm 1\%$) @ Addr Pin	SVID Address	Frequency	WP_Slew_TT REG5Bh (Default)	Protocol ID REG05h (Default)
0 to 88.7k	0000b – 1011b	Set via MODE table	1Bh	07h = VR13, 5 mV VID or 04h = VR13, 10 mV VID
105k	0001b	Set Via MODE table	5Bh	09h = VR14, 5 mV VID or 0Ah = VR14, 10 mV VID
127k	0001b	400kHz	1Bh	09h = VR14, 5 mV VID or 0Ah = VR14, 10 mV VID
150k	0001b	Set via MODE table	1Bh	09h = VR14, 5 mV VID or 0Ah = VR14, 10 mV VID
Float	0001b	400kHz	5Bh	09h = VR14, 5 mV VID or 0Ah = VR14, 10 mV VID

ICC_MAX and I_OUT

The NCP3285F/AF reports output current IOUT as a linear fraction of a full-scale output current available at a given time. The full-scale output current named IMAX has 9 discrete levels, which is selected according to the current limit set in the application. The NCP3285F/AF detects external resistance Rlim at Ilim pin during system reset time before soft start and stores a corresponding IMAX

value into Icc_Max register as shown in Table 9. The real output current value IOUT can be obtained from the reading I_out in the register 0x15h with a converting factor of IMAX/255.

$$I_{OUT} = \frac{I_{out_{15h}}}{255} \times I_{MAX} \quad (\text{eq. 1})$$

Table 9. ICC_MAX PROGRAMMING

Resistance ($\pm 1\%$) @ Ilim Pin	I _{MAX} (A)	ICC_MAX Register (21h)	Valley Current Limit (A)
R _{LIM} = 52.3 k Ω	45	2Dh	50
R _{LIM} = 47.5 k Ω	40	28h	45
R _{LIM} = 42.2 k Ω	35	23h	40
R _{LIM} = 36.5 k Ω	30	1Eh	35
R _{LIM} = 31.6 k Ω	25	19h	30
R _{LIM} = 26.1 k Ω	20	14h	25
R _{LIM} = 21.0 k Ω	15	0Fh	20
R _{LIM} = 15.4 k Ω	10	0Ah	15
R _{LIM} = 10.2 k Ω	5	05h	10

Enable and Input UVLO

The NCP3285F/AF is enabled when the voltage at EN pin is higher than an internal threshold V_{EN_TH}. A hysteresis can be programmed by an external resistor R_{EN} connected

to EN pin as shown in Figure 16. The high threshold V_{EN_H} in ENABLE signal is:

$$V_{EN_H} = V_{EN_TH} \quad (\text{eq. 2})$$

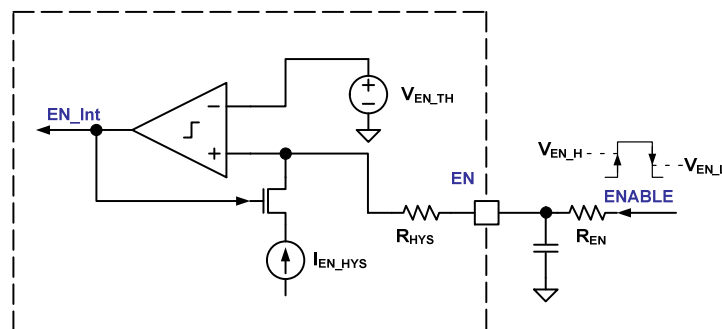


Figure 16. Enable and Hysteresis Programming

The low threshold V_{EN_L} in ENABLE signal is:

$$V_{EN_L} = V_{EN_TH} - V_{EN_HYS} \quad (\text{eq. 3})$$

The hysteresis V_{EN_HYS} is:

$$V_{EN_HYS} = I_{EN_HYS} \times (R_{HYS} + R_{EN}) \quad (\text{eq. 4})$$

A UVLO function for input power supply can be implemented at EN pin. As shown in Figure 17, the UVLO threshold can be programmed by two external resistors. The high threshold V_{IN_H} in VIN signal is:

$$V_{IN_H} = \left(\frac{R_{EN1}}{R_{EN2}} + 1 \right) \times V_{EN_TH} \quad (\text{eq. 5})$$

The low threshold V_{IN_L} in VIN signal is:

$$V_{IN_L} = V_{IN_H} - V_{IN_HYS} \quad (\text{eq. 6})$$

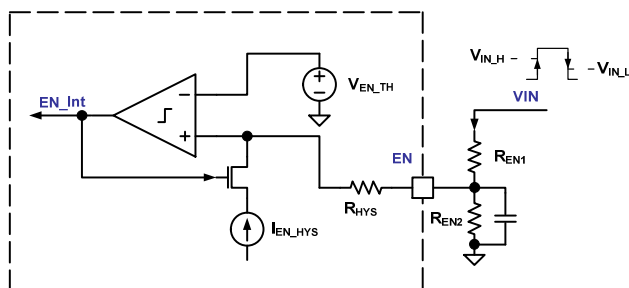


Figure 17. Enable and Input Supply UVLO Circuit

The hysteresis V_{IN_HYS} is:

$$V_{IN_HYS} = I_{EN_HYS} \times \left(R_{HYS} \left(1 + \frac{R_{EN1}}{R_{EN2}} \right) + R_{EN1} \right), \quad (\text{eq. 7})$$

To avoid undefined operation, EN pin should not be left float in applications.

Over Current Protection (OCP)

The NCP3285F/AF protects converter from over current by a cycle-by-cycle current limitation. The average current limit I_{LMT} can be calculated from the programmed valley current limit I_{LMT_Valley} and inductor current ripple as shown in (eq. 8).

where R_{lim} is resistance of the programming resistor at Ilim pin, V_{IN} is input voltage, V_O is output voltage, L is filter inductance, and F_{SW} is nominal switching frequency.

$$I_{LMT} = I_{LMT_Valley} + \frac{V_O \times (V_{IN} - V_O)}{2 \times V_{IN} \times L \times F_{SW}} = 9.62 \times 10^{-4} \times R_{lim} + \frac{V_O \times (V_{IN} - V_O)}{2 \times V_{IN} \times L \times F_{SW}} \quad (\text{eq. 8})$$

Under Voltage Protection (UVP)

UVP detection starts when PGOOD delay T_{d_PGOOD} is expired right after soft start, and ends in shutdown. The NCP3285F/AF pulls PGOOD low and turns off both high-side and low-side MOSFETs once FB voltage drops below 0.2 V for more than 1.0 μ s. To restart the device after UVP latch-off, the system needs to have either VCC or EN toggled state.

Over Voltage Protection (OVP)

OVP detection starts from the beginning of soft-start time TSS and ends in shutdown. During normal operation the output voltage is monitored at FB pin. If FB voltage exceeds the OVP threshold for more than 1 μ s, OVP is triggered and

OCP detection starts from beginning of soft-start time TSS, and ends in shutdown. Inductor current is monitored by voltage sensing between SW pin and PGND pin. If over current happens and lasts for more than 50 μ s, the device latches off. The device may trip under voltage protection before OCP latch-off if output voltage drops down very fast. To restart the device after OCP latch-off, the system needs to have either VCC or EN toggled state.

PGOOD is pulled low. In the meanwhile, the high-side MOSFET is latched off and the low-side MOSFET is turned on. After the OVP trips, the DAC ramps slowly down to zero, having a negative slew rate as the same value of soft start to reduce negative output voltage spike. The low-side MOSFET toggles between on and off as the output voltage follows the OVP threshold down with a hysteresis. After the DAC gets to zero, the high-side MOSFET holds off and the low-side MOSFET keeps on. During soft-start, the OVP threshold is set to a fixed value of 2.0 V, and it changes to DAC + 200 mV after DAC starts to ramp down due to OVP. To restart the device from OVP latch-off, the system needs to have either VCC or EN toggled state.

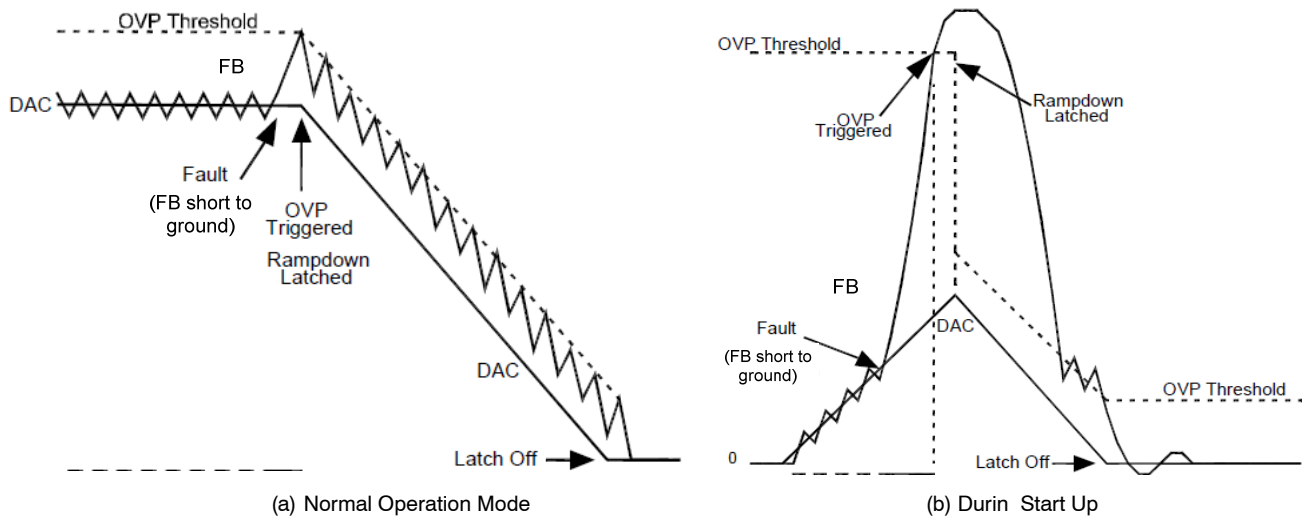


Figure 18. Function of Over Voltage Protection

Thermal Shutdown (TSD)

The NCP3285F/AF has an internal thermal shutdown protection to protect the device from overheating in an extreme case that the die temperature exceeds 150°C. TSD detection is activated when VCC and EN are valid. Once the

thermal protection is triggered, the whole chip shuts down. If the temperature drops below 125°C, the system automatically recovers and a normal power-up sequence follows.

LAYOUT GUIDELINES

Electrical Layout Considerations

Good electrical layout is a key to make sure proper operation, high efficiency, and noise reduction. Electrical layout guidelines are:

- **Power Paths:** Use wide and short traces for power paths (such as VIN, VOUT, SW, and PGND) to reduce parasitic inductance and high-frequency loop area. It is also good for efficiency improvement
- **Power Supply Decoupling:** The device should be well decoupled by input capacitors and input loop area should be as small as possible to reduce parasitic inductance, input voltage spike, and noise emission. Usually, a small low-ESL MLCC is placed very close to PVIN and PGND pins
- **VCC Decoupling:** Place decoupling caps as close as possible to the controller VCC and VDRV pins. The filter resistor at VCC pin should be not higher than $2.2\ \Omega$ to prevent large voltage drop
- **Switching Node:** SW node should be a copper pour, but compact because it is also a noise source
- **Bootstrap:** The bootstrap cap and an option resistor need to be very close and directly connected between pin 26 (BST) and pin 25 (PHASE). No need to externally connect pin 25 to SW node because it has been internally connected to other SW pins
- **Ground:** It would be good to have multiple ground planes. Directly connect the exposed PGND pad to

ground plane through multiple vias. Connect AGND pin to ground planes through a via close to the pin

- **Voltage Sense:** Use Kelvin sense pair and arrange a “quiet” path for the differential output voltage sense. Keep the FB trace short to minimize its capacitance to ground
- **SVID Bus:** The Serial VID bus is a high speed data bus and the bus routing should be done to limit noise coupling from the switching node. The SVID lines must be ground referenced and each line’s width and spacing should be such that they have nominal $50\ \Omega$ impedance with the board stackup. For details, please refer to Intel SVID routing guidelines

Thermal Layout Considerations

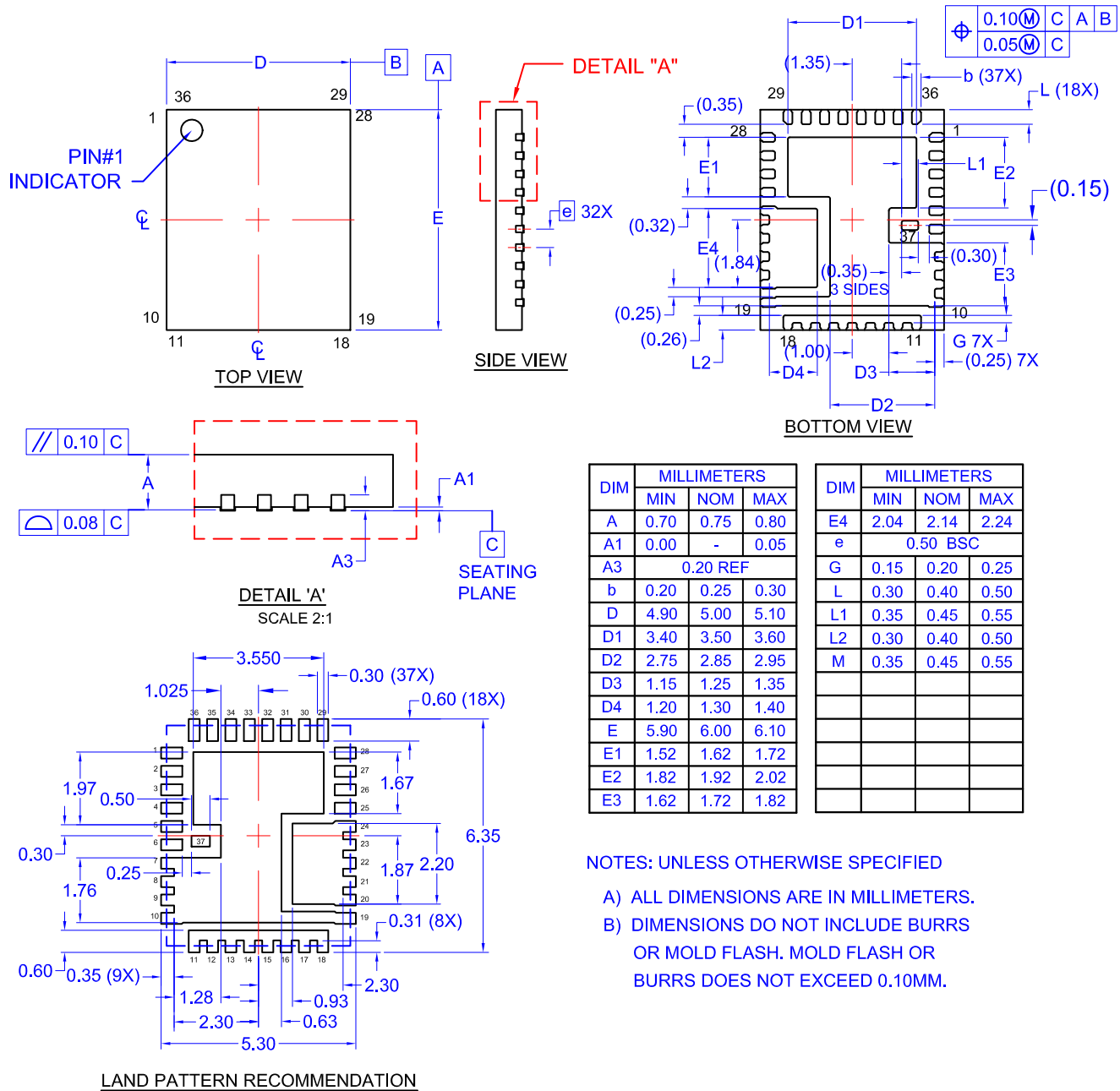
Good thermal layout helps high power dissipation from a small package with reduced temperature rise. Thermal layout guidelines are:

- The exposed pads must be well soldered on the board
- A four or more layers PCB board with solid ground planes is preferred for better heat dissipation
- More free vias are welcome to be around IC and underneath the exposed pads to connect the inner ground layers to reduce thermal impedance
- Use large area copper pour to help thermal conduction and radiation
- Do not put the inductor to be too close to the IC, thus the heat sources are distributed

PACKAGE DIMENSIONS

PQFN37 5x6, 0.5P
CASE 483BZ
ISSUE O

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